

# RT2C00M

COMPOSITE TRANSISTOR  
FOR LOW FREQUENCY AMPLIFY APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

RT2C00M is a composite transistor built with two 2SC3052 chips in SC-88 package.

## FEATURE

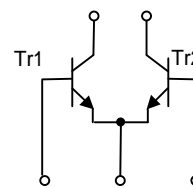
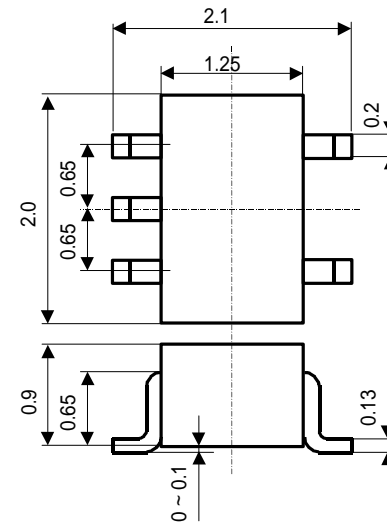
- Silicon npn epitaxial type
- Each transistor elements are independent.
- Mini package for easy mounting

## APPLICATION

For low frequency amplify application

## OUTLINE DRAWING

Unit:mm



### TERMINAL CONNECTOR

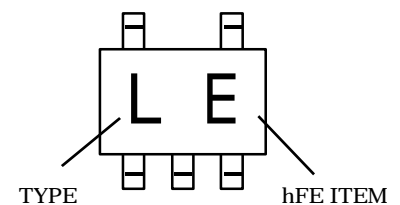
- : BASE 1
- : EMITTER (COMMON)
- : BASE 2
- : COLLECTOR 2
- : COLLECTOR 1

JEITA : -  
JEDEC : -

## MAXIMUM RATINGS (Ta=25 °C)(Tr1, Tr2)

Symbol	Parameter	Ratings	Unit
$V_{CBO}$	Collector to Base voltage	50	V
$V_{EBO}$	Emitter to Base voltage	6	V
$V_{CEO}$	Collector to Emitter voltage	50	V
$I_C$	Collector current	200	mA
$P_C$	Collector dissipation (Total Ta=25 °C)	150	mW
$T_j$	Junction temperature	+ 125	
$T_{stg}$	Storage temperature	-55 ~ + 125	

## MARKING



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## ELECTRICAL CHARACTERISTICS (Ta=25 °C)(Tr1, Tr2)

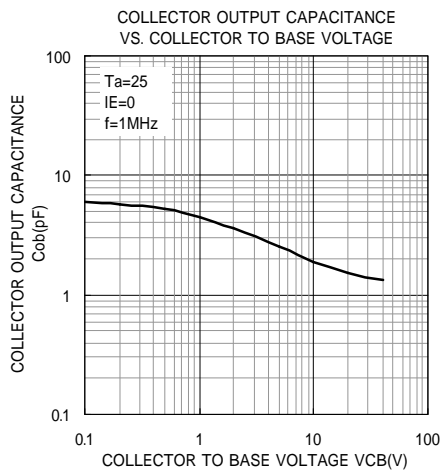
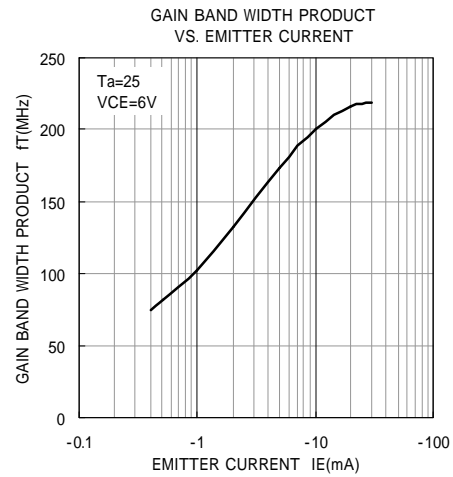
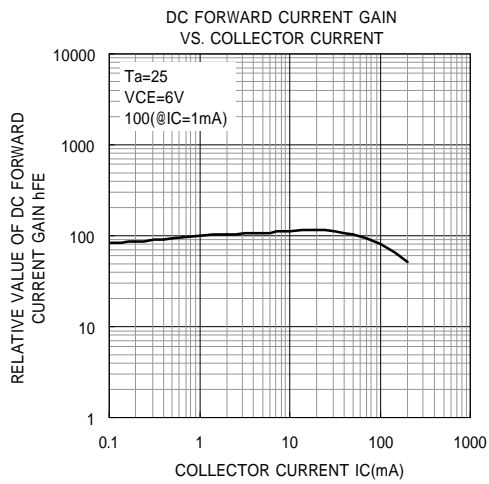
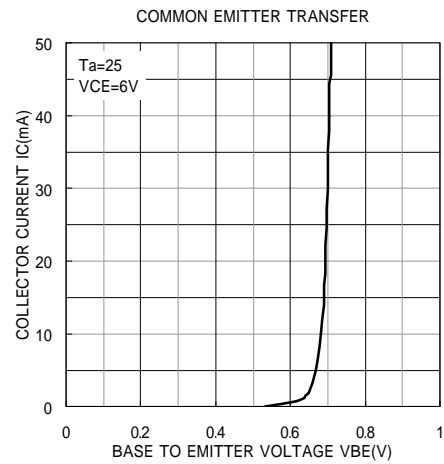
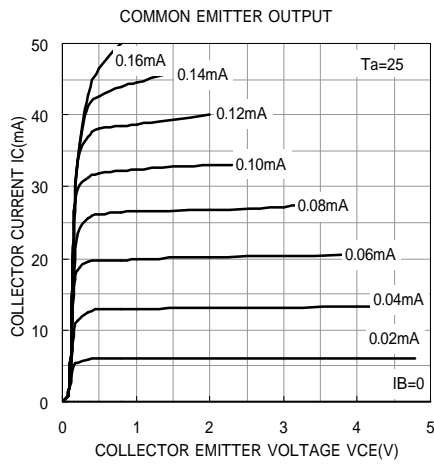
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	Collector to Emitter break down voltage	$I_C=100 \mu A, R_{BE}=\infty$	50	-	-	V
$I_{CBO}$	Collector cut off current	$V_{CB}=50V, I_E=0mA$	-	-	0.1	$\mu A$
$I_{EBO}$	Emitter cut off current	$V_{EB}=6V, I_C=0mA$	-	-	0.1	$\mu A$
$h_{FE}^*$	DC forward current gain	$V_{CE}=6V, I_C=1mA$	150	-	800	-
$h_{FE}$	DC forward current gain	$V_{CE}=6V, I_C=0.1mA$	90	-	-	-
$V_{CE(sat)}$	Collector to Emitter saturation voltage	$I_C=100mA, I_B=10mA$	-	-	0.3	V
$f_T$	Gain band width product	$V_{CE}=6V, I_E=10mA$	-	200	-	MHz
Cob	Collector output capacitance	$V_{CB}=6V, I_E=0mA, f=1MHz$	-	2.5	-	pF
NF	Noise figure	$V_{CE}=6V, I_E=0.1mA, f=100Hz, R_G=2k$	-	-	15	dB

\* : It shows  $h_{FE}$  classification in right table.

ITEM	E	F	G
$h_{FE}$	150 ~ 300	250 ~ 500	400 ~ 800
MARKING	LE	LF	LG

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